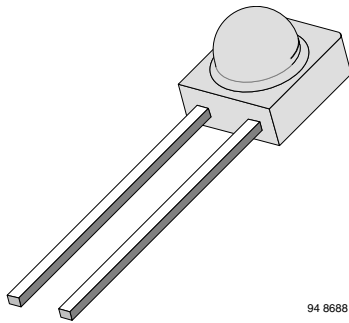


## High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



### DESCRIPTION

TSSF4500 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (L x W x H in mm): 4.5 x 4 x 4.8
- Peak wavelength:  $\lambda_p = 890$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth:  $f_c = 12$  MHz
- Good spectral matching with Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



### Note

\*\* Please see document "Vishay Material Category Policy":  
[www.vishay.com/doc?99902](http://www.vishay.com/doc?99902)

### APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- TSSF4500 is ideal for the design of transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)

### PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\phi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|--------------|------------------|------------|
| TSSF4500  | 20            | $\pm 22$     | 890              | 30         |

### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| TSSF4500      | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | Side view    |

### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER             | TEST CONDITION                       | SYMBOL    | VALUE | UNIT |
|-----------------------|--------------------------------------|-----------|-------|------|
| Reverse voltage       |                                      | $V_R$     | 5     | V    |
| Forward current       |                                      | $I_F$     | 100   | mA   |
| Peak forward current  | $t_p/T = 0.5, t_p = 100 \mu\text{s}$ | $I_{FM}$  | 200   | mA   |
| Surge forward current | $t_p = 100 \mu\text{s}$              | $I_{FSM}$ | 1.5   | A    |
| Power dissipation     |                                      | $P_V$     | 160   | mW   |

| <b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified) |                                      |            |               |                    |
|--|--------------------------------------|------------|---------------|--------------------|
| PARAMETER  | TEST CONDITION                       | SYMBOL     | VALUE         | UNIT               |
| Junction temperature   |                                      | $T_j$      | 100           | $^{\circ}\text{C}$ |
| Operating temperature range  |                                      | $T_{amb}$  | - 40 to + 100 | $^{\circ}\text{C}$ |
| Storage temperature range  |                                      | $T_{stg}$  | - 40 to + 100 | $^{\circ}\text{C}$ |
| Soldering temperature  | $t \leq 5\text{ s}$ , 2 mm from case | $T_{sd}$   | 260           | $^{\circ}\text{C}$ |
| Thermal resistance junction/ambient  | Leads not soldered                   | $R_{thJA}$ | 450           | K/W                |

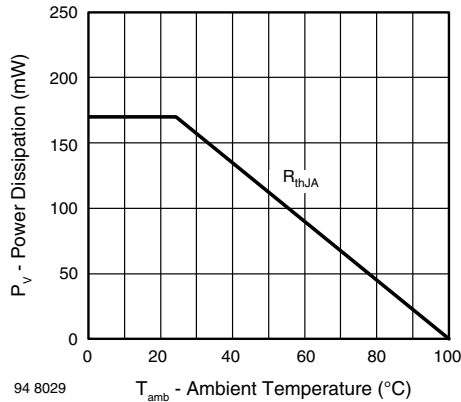


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

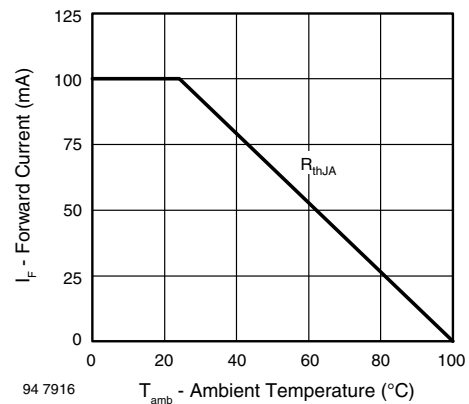


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| <b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified) |   |                  |      |          |      |               |
|---|---|------------------|------|----------|------|---------------|
| PARAMETER   | TEST CONDITION  | SYMBOL           | MIN. | TYP.     | MAX. | UNIT          |
| Forward voltage   | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$          | $V_F$            |      | 1.35     | 1.6  | V             |
|   | $I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$ | $V_F$            |      | 2.4      |      | V             |
| Temperature coefficient of $V_F$  | $I_F = 1\text{ mA}$                                   | $TK_{V_F}$       |      | - 1.8    |      | mV/K          |
| Reverse current   | $V_R = 5\text{ V}$                                    | $I_R$            |      |          | 10   | $\mu\text{A}$ |
| Junction capacitance  | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$     | $C_j$            |      | 160      |      | pF            |
| Radiant intensity   | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$          | $I_e$            | 10   | 20       | 50   | mW/sr         |
|   | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$   | $I_e$            |      | 200      |      | mW/sr         |
| Radiant power   | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$          | $\phi_e$         |      | 35       |      | mW            |
| Temperature coefficient of $\phi_e$   | $I_F = 100\text{ mA}$                                 | $TK_{\phi_e}$    |      | - 0.7    |      | %/K           |
| Angle of half intensity   |   | $\phi$           |      | $\pm 22$ |      | deg           |
| Peak wavelength   | $I_F = 100\text{ mA}$                                 | $\lambda_p$      |      | 890      |      | nm            |
| Spectral bandwidth  | $I_F = 100\text{ mA}$                                 | $\Delta\lambda$  |      | 40       |      | nm            |
| Temperature coefficient of $\lambda_p$  | $I_F = 100\text{ mA}$                                 | $TK_{\lambda_p}$ |      | 0.2      |      | nm/K          |
| Rise time   | $I_F = 100\text{ mA}$                                 | $t_r$            |      | 30       |      | ns            |
| Fall time   | $I_F = 100\text{ mA}$                                 | $t_f$            |      | 30       |      | ns            |
| Cut-off frequency   | $I_{DC} = 70\text{ mA}$ , $I_{AC} = 30\text{ mA pp}$  | $f_c$            |      | 12       |      | MHz           |
| Virtual source diameter   |   | $d$              |      | 2.1      |      | mm            |

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

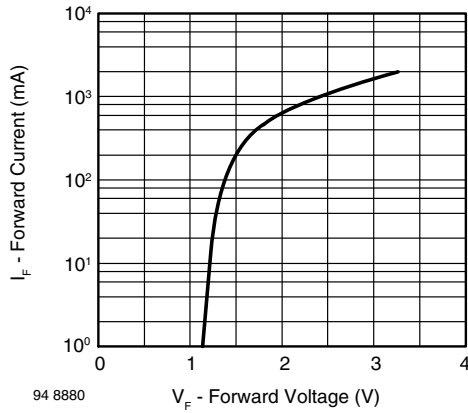


Fig. 3 - Forward Current vs. Forward Voltage

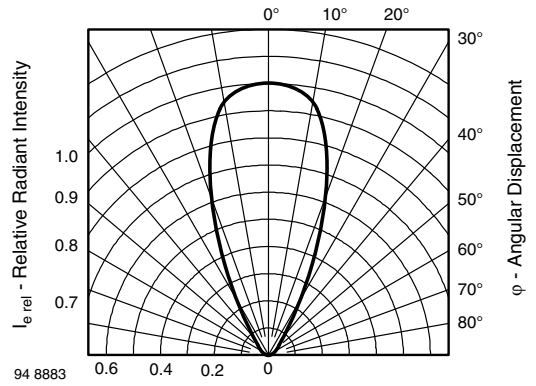


Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

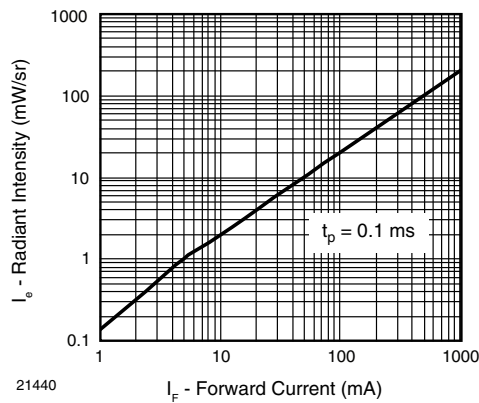


Fig. 4 - Radiant Intensity vs. Forward Current

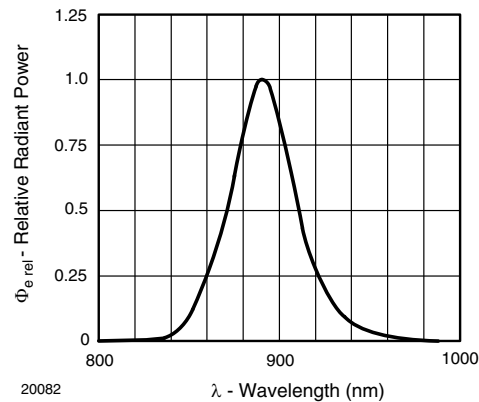
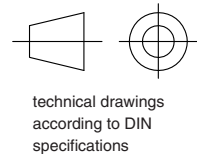
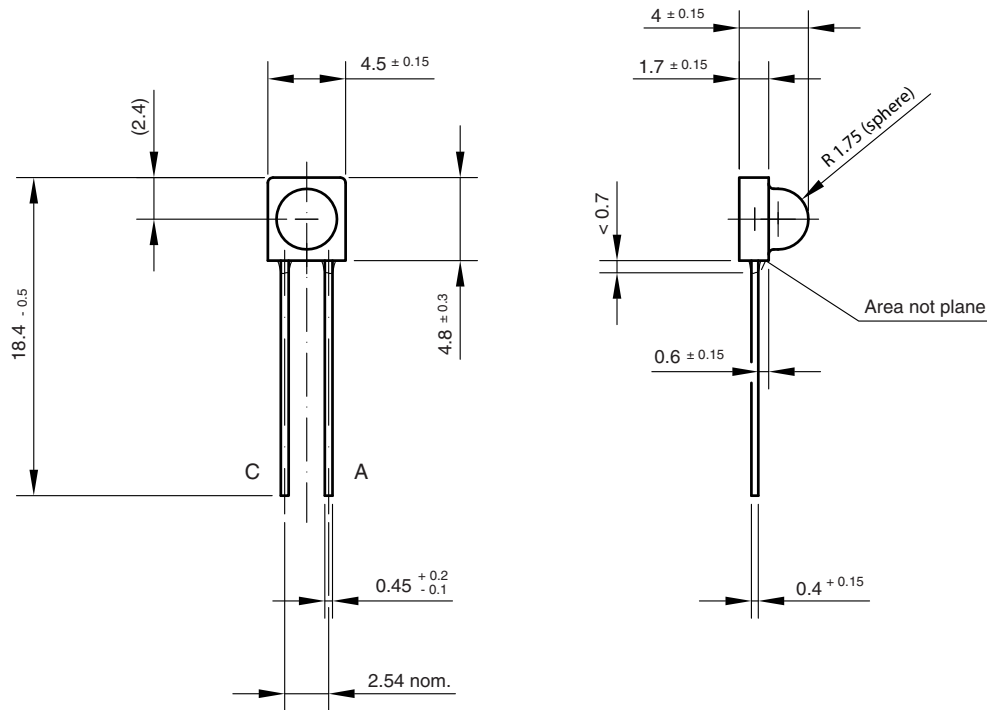


Fig. 5 - Relative Radiant Power vs. Wavelength



**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.544-5253.01-4

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